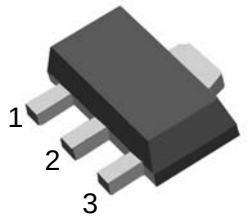
Transys Electronics LIMITED

SOT-89 Plastic-Encapsulated Transistors

2SA1201 TRANSISTOR (PNP)

SOT-89

1. BASE
2. COLLECTOR
3. EMITTER



FEATURES

Power dissipation

P_{CM} : 500 mW (Tamb=25℃)

Collector current

I_{CM} : -800 mA

Collector-base voltage

$V_{(BR)CBO}$: -120 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=-1mA, I_E=0	-120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic=-10mA, I_B=0	-120			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-1mA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-120V, I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0			-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-5V, I_C=-100mA	80		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA			-1	V
Base-emitter voltage	V_{BE}	V_{CE}=-5V, I_C=-500mA			-1	V
Transition frequency	f_T	V_{CE}=-5V, I_C=-100mA		120		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz			30	pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	80-160	120-240
Marking	DO	DY